

2N3859A

NPN General Purpose Amplifier

- This device designed for use as general purpose amplifier and switches requiring collector currents to 300mA.
- · Sourced from Process 10.
- See PN100 for characteristics.



1. Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{ST}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Characteristics						
BV _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_C = 1.0 \text{mA}, I_B = 0$	60			V
BV _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	60			V
BV _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6.0			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 18V, I_{E} = 0$			0.5	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 4.0V, I_{C} = 0$			0.5	μΑ
On Characteristics *						
h _{FE}	DC Current Gain	V _{CE} = 1.0V, I _C = 1.0mA	75			
		$V_{CE} = 1.0V, I_{C} = 1.0mA$	100		200	
Small Signal Characteristics						
C _{ob}	Current Gain Bandwidth Product	V _{CB} = 10V, f = 1.0MHz			4	pF
f _T	Output Capacitance	$I_C = 2.0 \text{mA}, V_{CE} = 10 \text{V}$	90		250	MHz
rb'C _c	Collector-Base Time Constant	$V_{CE} = 10V, I_{C} = 2.0mA$			150	pS
		f = 31.9MHz				

^{*} Pulse Test: Pulse ≤ 300μs, Duty Cycle ≤ 2.0%

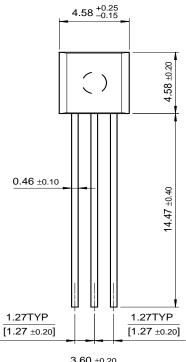
Thermal Characteristics T_A=25°C unless otherwise noted

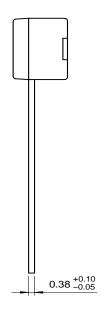
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

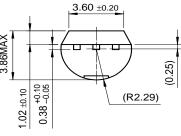
These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Package Dimensions

TO-92







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